

AF114, AF115, AF116

Germaniové tranzistory Mullard pro radiotechniku

RADIOX
LABORATORIES

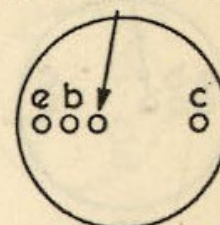
COMPONENT BASE

R.F. P-N-P alloy diffused junction transistor—AF114

P _{tot} max. (T _{amb} ≤ 45°C)	50	mW
θ _{j-amb}	0.6	°C/mW
V _{CB} max. (I _E = 0)	-20	V
I _{CM} max.	10	mA
f _T typ (I _E = 1.0mA, V _{CB} = 6V)	75	Mc/s
C _{obs} typ (I _E = 1.0mA, V _{CB} = 6V)		
AF114 (100Mc/s)	2.5	pF
AF115 (100Mc/s)	2.5	pF

At frequencies below 10.7Mc/s the feedback capacitance in grounded emitter (C_{oes}) is approximately 3.5pF; at I_E = 1.0 mA, V_{CB} = 6V

interlead shield
and metal case



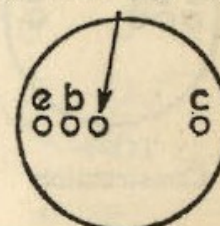
TO-7
Construction

0C171

R.F. P-N-P alloy diffused junction transistor—AF115

Measured at T _{amb} = 25°C		
V _{CB}	-20	V
I _C (Ar) max.	10	mA
f	1.0	kc/s
h _{fe}	150	
P _{tot} max. (T _{amb} = 45°C)	50	mW
θ _{j-amb}	≤ 0.6	°C/mW
Power gain (f = 100 Mc/s)	13	dB

interlead shield
and metal case

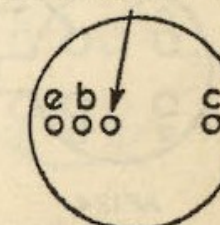


TO-7
Construction

R.F. P-N-P alloy diffused junction transistor—AF116

Measured at T _{amb} = 25°C		
V _{CB}	-20	V
I _C (Ar) max.	10	mA
f	1.0	kc/s
h _{fe}	150	
P _{tot} max. (T _{amb} = 45°C)	50	mW
θ _{j-amb}	≤ 0.6	°C/mW
Power gain (f = 10.7 Mc/s)	25	dB

interlead shield
and metal case



TO-7
Construction

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Největší česká databáze elektronických součástí